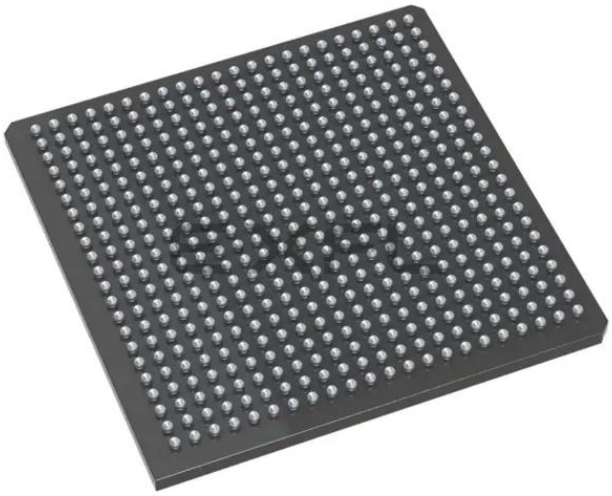

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Embedded - System On Chip (SoC): The Heart of Modern Embedded Systems

Embedded - System On Chip (SoC) refers to an integrated circuit that consolidates all the essential components of a computer system into a single chip. This includes a microprocessor, memory, and other peripherals, all packed into one compact and efficient package. SoCs are designed to provide a complete computing solution, optimizing both space and power consumption, making them ideal for a wide range of embedded applications.

What are Embedded - System On Chip (SoC)?

System On Chip (SoC) integrates multiple functions of a computer or electronic system onto a single chip. Unlike traditional multi-chip solutions, SoCs combine a central

Details	
Product Status	Active
Architecture	MCU, FPGA
Core Processor	ARM® Cortex®-M3
Flash Size	256KB
RAM Size	64KB
Peripherals	DMA, POR, WDT
Connectivity	EBI/EMI, Ethernet, I²C, SPI, UART/USART
Speed	80MHz
Primary Attributes	ProASIC®3 FPGA, 200K Gates, 4608 D-Flip-Flops
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	484-BGA
Supplier Device Package	484-FPBGA (23x23)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/a2f200m3f-fgg484i

Email: info@E-XFL.COM Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

$$P = \frac{T_J - T_A}{\theta_{JA}} = \frac{100°C - 70°C}{17.00\ W} = 1.76\ W$$

EQ 6

The 1.76 W power is less than the required 3.00 W. The design therefore requires a heat sink, or the airflow where the device is mounted should be increased. The design's total junction-to-air thermal resistance requirement can be estimated by EQ 7:

$$\theta_{JA(total)} = \frac{T_J - T_A}{P} = \frac{100°C - 70°C}{3.00\ W} = 10.00°C/W$$

EQ 7

Determining the heat sink's thermal performance proceeds as follows:

$$\theta_{JA(TOTAL)} = \theta_{JC} + \theta_{CS} + \theta_{SA}$$

EQ 8

where

θ_{JA} = 0.37°C/W

= Thermal resistance of the interface material between the case and the heat sink, usually provided by the thermal interface manufacturer

θ_{SA} = Thermal resistance of the heat sink in °C/W

$$\theta_{SA} = \theta_{JA(TOTAL)} - \theta_{JC} - \theta_{CS}$$

EQ 9

$$\theta_{SA} = 13.33°C/W - 8.28°C/W - 0.37°C/W = 5.01°C/W$$

A heat sink with a thermal resistance of 5.01°C/W or better should be used. Thermal resistance of heat sinks is a function of airflow. The heat sink performance can be significantly improved with increased airflow.

Carefully estimating thermal resistance is important in the long-term reliability of an FPGA. Design engineers should always correlate the power consumption of the device with the maximum allowable power dissipation of the package selected for that device.

Note: The junction-to-air and junction-to-board thermal resistances are based on JEDEC standard (JESD-51) and assumptions made in building the model. It may not be realized in actual application and therefore should be used with a degree of caution. Junction-to-case thermal resistance assumes that all power is dissipated through the case.

Temperature and Voltage Derating Factors

Table 2-7 • **Temperature and Voltage Derating Factors for Timing Delays (normalized to T_J = 85°C, worst-case VCC = 1.425 V)**

Array Voltage VCC (V)	Junction Temperature (°C)					
	–40°C	0°C	25°C	70°C	85°C	100°C
1.425	0.86	0.91	0.93	0.98	1.00	1.02
1.500	0.81	0.86	0.88	0.93	0.95	0.96
1.575	0.78	0.83	0.85	0.90	0.91	0.93

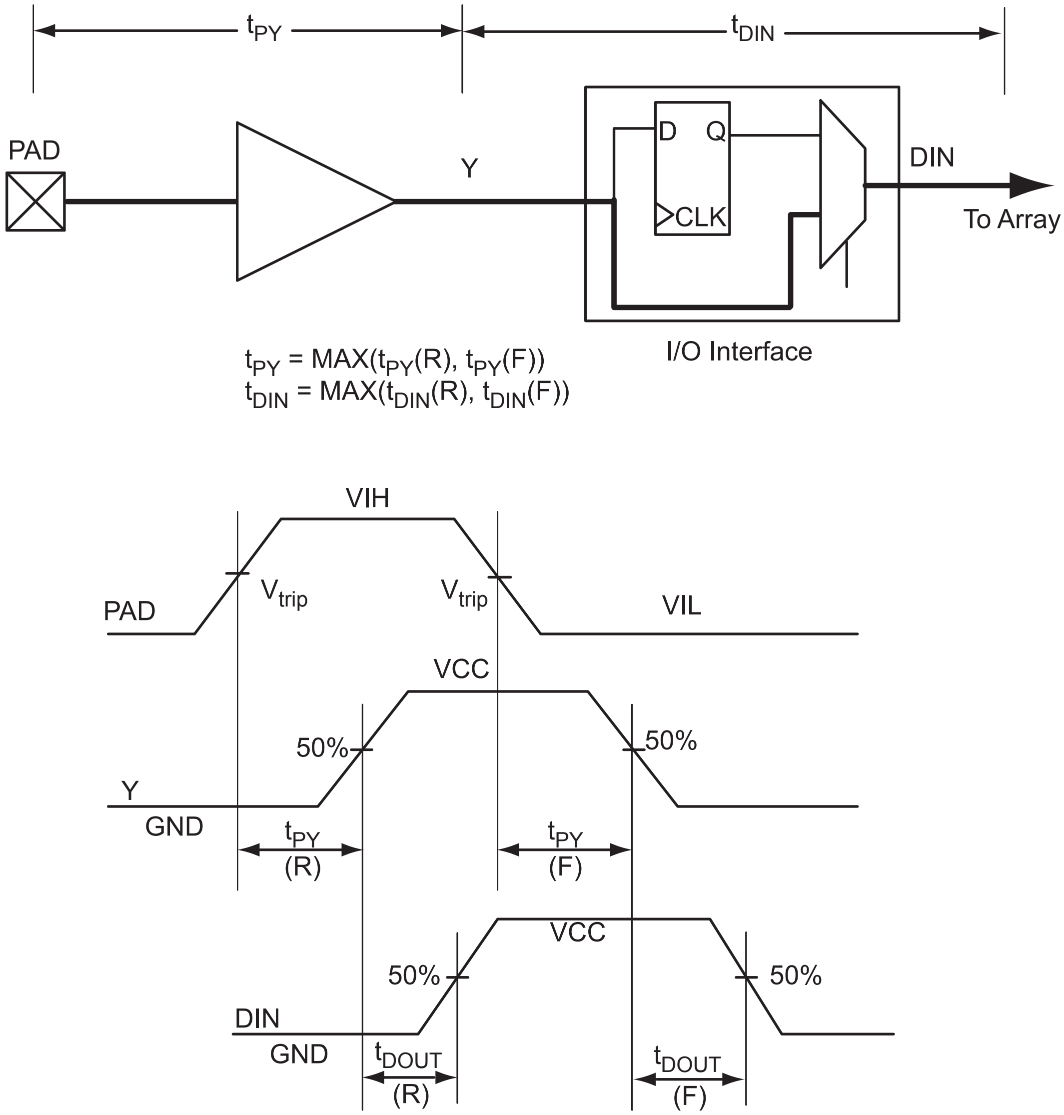


Figure 2-3 • **Input Buffer Timing Model and Delays (example)**

Detailed I/O DC Characteristics

Table 2-26 **• Input Capacitance**

Symbol	Definition	Conditions	Min.	Max.	Units
C_{IN}	Input capacitance	V_{IN} = 0, f = 1.0 MHz		8	pF
C_{INCLK}	Input capacitance on the clock pin	V_{IN} = 0, f = 1.0 MHz		8	pF

Table 2-27 **• I/O Output Buffer Maximum Resistances[1]**
Applicable to FPGA I/O Banks

Standard	Drive Strength	$R_{PULL\text{-}DOWN}$ (Ω)[2]	$R_{PULL\text{-}UP}$ (Ω)[3]
3.3 V LVTTL / 3.3 V LVCMOS	2 mA	100	300
	4 mA	100	300
	6 mA	50	150
	8 mA	50	150
	12 mA	25	75
	16 mA	17	50
	24 mA	11	33
2.5 V LVCMOS	2 mA	100	200
	4 mA	100	200
	6 mA	50	100
	8 mA	50	100
	12 mA	25	50
	16 mA	20	40
	24 mA	11	22
1.8 V LVCMOS	2 mA	200	225
	4 mA	100	112
	6 mA	50	56
	8 mA	50	56
	12 mA	20	22
	16 mA	20	22
1.5 V LVCMOS	2 mA	200	224
	4 mA	100	112
	6 mA	67	75
	8 mA	33	37
	12 mA	33	37
3.3 V PCI/PCI-X	Per PCI/PCI-X specification	25	75

Notes:

1. *These maximum values are provided for information only. Minimum output buffer resistance values depend on VCCxxxxIOBx, drive strength selection, temperature, and process. For board design considerations and detailed output buffer resistances, use the corresponding IBIS models located on the Microsemi SoC Products Group website (also generated by the SoC Products Group Libero SoC toolset).*
2. $R_{(PULL\text{-}DOWN\text{-}MAX)} = (V_{OLspec}) / I_{OLspec}$
3. $R_{(PULL\text{-}UP\text{-}MAX)} = (V_{CCImax} - V_{OHspec}) / I_{OHspec}$

Table 2-28 **• I/O Output Buffer Maximum Resistances[1]**
Applicable to MSS I/O Banks

Standard	Drive Strength	$R_{PULL\text{-}DOWN}$ (Ω)[2]	$R_{PULL\text{-}UP}$ (Ω)[3]
3.3 V LVTTL / 3.3 V LVCMOS	8mA	50	150
2.5 V LVCMOS	8 mA	50	100
1.8 V LVCMOS	4 mA	100	112
1.5 V LVCMOS	2 mA	200	224

Notes:

1. *These maximum values are provided for informational reasons only. Minimum output buffer resistance values depend on VCCxxxxIOBx, drive strength selection, temperature, and process. For board design considerations and detailed output buffer resistances, use the corresponding IBIS models located on the Microsemi SoC Products Group website.*
2. $R_{(PULL\text{-}DOWN\text{-}MAX)} = (V_{OLspec}) / I_{OLspec}$
3. $R_{(PULL\text{-}UP\text{-}MAX)} = (V_{CCImax} - V_{OHspec}) / I_{OHspec}$

Table 2-29 **• I/O Weak Pull-Up/Pull-Down Resistances**
Minimum and Maximum Weak Pull-Up/Pull-Down Resistance Values

VCCxxxxIOBx	$R_{(WEAK\ PULL\text{-}UP)}$[1] (Ω)		$R_{(WEAK\ PULL\text{-}DOWN)}$[2] (Ω)	
	Min.	Max.	Min.	Max.
3.3 V	10 k	45 k	10 k	45 k
2.5 V	11 k	55 k	12 k	74 k
1.8 V	18 k	70 k	17 k	110 k
1.5 V	19 k	90 k	19 k	140 k

Notes:

1. $R_{(WEAK\ PULL\text{-}UP\text{-}MAX)} = (VCCImax - VOHspec) / I_{(WEAK\ PULL\text{-}UP\text{-}MIN)}$
2. $R_{(WEAK\ PULL\text{-}DOWN\text{-}MAX)} = (VOLspec) / I_{(WEAK\ PULL\text{-}DOWN\text{-}MIN)}$

Table 2-30 **• I/O Short Currents I_{OSH}/I_{OSL}**
Applicable to FPGA I/O Banks

	Drive Strength	I_{OSL} (mA)*	I_{OSH} (mA)*
3.3 V LVTTL / 3.3 V LVCMOS	2 mA	27	25
	4 mA	27	25
	6 mA	54	51
	8 mA	54	51
	12 mA	109	103
	16 mA	127	132
	24 mA	181	268
2.5 V LVCMOS	2 mA	18	16
	4 mA	18	16
	6 mA	37	32
	8 mA	37	32
	12 mA	74	65
	16 mA	87	83
	24 mA	124	169
1.8 V LVCMOS	2 mA	11	9
	4 mA	22	17
	6 mA	44	35
	8 mA	51	45
	12 mA	74	91
	16 mA	74	91
1.5 V LVCMOS	2 mA	16	13
	4 mA	33	25
	6 mA	39	32
	8 mA	55	66
	12 mA	55	66
3.3 V PCI/PCI-X	Per PCI/PCI-X specification	109	103

Note: *T_J = 85°C.*

Table 2-31 **• I/O Short Currents I_{OSH}/I_{OSL}**
Applicable to MSS I/O Banks

	Drive Strength	I_{OSL} (mA)*	I_{OSH} (mA)*
3.3 V LVTTL / 3.3 V LVCMOS	8 mA	54	51
2.5 V LVCMOS	8 mA	37	32
1.8 V LVCMOS	4 mA	22	17
1.5 V LVCMOS	2 mA	16	13

Note: *T_J = 85°C*

1.8 V LVCMOS

Low-voltage CMOS for 1.8 V is an extension of the LVCMOS standard (JESD8-5) used for general-purpose 1.8 V applications. It uses a 1.8 V input buffer and a push-pull output buffer.

Table 2-47 • Minimum and Maximum DC Input and Output Levels Applicable to FPGA I/O Banks

1.8 V LVCMOS	VIL		VIH		VOL	VOH	I_{OL}	I_{OH}	I_{OSL}	I_{OSH}	I_{IL}	I_{IH}
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA[1]	Max. mA[1]	µA[2]	µA[2]
2 mA	–0.3	0.35 * VCCxxxxIOBx	0.65 * VCCxxxxIOBx	1.9	0.45	VCCxxxxIOBx – 0.45	2	2	11	9	15	15
4 mA	–0.3	0.35 * VCCxxxxIOBx	0.65 * VCCxxxxIOBx	1.9	0.45	VCCxxxxIOBx – 0.45	4	4	22	17	15	15
6 mA	–0.3	0.35 * VCCxxxxIOBx	0.65 * VCCxxxxIOBx	1.9	0.45	VCCxxxxIOBx – 0.45	6	6	44	35	15	15
8 mA	–0.3	0.35 * VCCxxxxIOBx	0.65 * VCCxxxxIOBx	1.9	0.45	VCCxxxxIOBx – 0.45	8	8	51	45	15	15
12 mA	–0.3	0.35 * VCCxxxxIOBx	0.65 * VCCxxxxIOBx	1.9	0.45	VCCxxxxIOBx – 0.45	12	12	74	91	15	15
16 mA	–0.3	0.35 * VCCxxxxIOBx	0.65 * VCCxxxxIOBx	1.9	0.45	VCCxxxxIOBx – 0.45	16	16	74	91	15	15

Notes:

1. *Currents are measured at high temperature (100°C junction temperature) and maximum voltage.*
2. *Currents are measured at 85°C junction temperature.*
3. *Software default selection highlighted in gray.*

Table 2-48 • Minimum and Maximum DC Input and Output Levels Applicable to MSS I/O Banks

1.8 V LVCMOS	VIL		VIH		VOL	VOH	I_{OL}	I_{OH}	I_{OSL}	I_{OSH}	I_{IL}	I_{IH}
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA[1]	Max. mA[1]	µA[2]	µA[2]
4 mA	–0.3	0.35 * VCCxxxxIOBx	0.65 * VCCxxxxIOBx	3.6	0.45	VCCxxxxIOBx – 0.45	4	4	22	17	15	15

Notes:

1. *Currents are measured at high temperature (100°C junction temperature) and maximum voltage.*
2. *Currents are measured at 85°C junction temperature.*
3. *Software default selection highlighted in gray.*

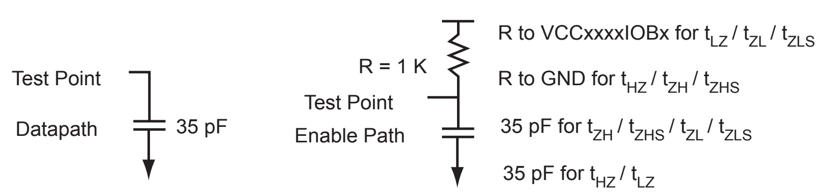


Figure 2-8 • AC Loading

Table 2-49 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	V_{REF} (typ.) (V)	C_{LOAD} (pF)
0	1.8	0.9	–	35

* *Measuring point = V_{trip}. See Table 2-22 on page 2-24 for a complete table of trip points.*

Table 2-70 • **Parameter Definition and Measuring Nodes**

Parameter Name	Parameter Definition	Measuring Nodes (from, to)*
t_{OCLKQ}	Clock-to-Q of the Output Data Register	HH, DOUT
t_{OSUD}	Data Setup Time for the Output Data Register	FF, HH
t_{OHD}	Data Hold Time for the Output Data Register	FF, HH
t_{OSUE}	Enable Setup Time for the Output Data Register	GG, HH
t_{OHE}	Enable Hold Time for the Output Data Register	GG, HH
t_{OCLR2Q}	Asynchronous Clear-to-Q of the Output Data Register	LL, DOUT
$t_{OREMCLR}$	Asynchronous Clear Removal Time for the Output Data Register	LL, HH
$t_{ORECCLR}$	Asynchronous Clear Recovery Time for the Output Data Register	LL, HH
t_{OECLKQ}	Clock-to-Q of the Output Enable Register	HH, EOUT
t_{OESUD}	Data Setup Time for the Output Enable Register	JJ, HH
t_{OEHD}	Data Hold Time for the Output Enable Register	JJ, HH
t_{OESUE}	Enable Setup Time for the Output Enable Register	KK, HH
t_{OEHE}	Enable Hold Time for the Output Enable Register	KK, HH
$t_{OECLR2Q}$	Asynchronous Clear-to-Q of the Output Enable Register	II, EOUT
$t_{OEREMCLR}$	Asynchronous Clear Removal Time for the Output Enable Register	II, HH
$t_{OERECCLR}$	Asynchronous Clear Recovery Time for the Output Enable Register	II, HH
t_{ICLKQ}	Clock-to-Q of the Input Data Register	AA, EE
t_{ISUD}	Data Setup Time for the Input Data Register	CC, AA
t_{IHD}	Data Hold Time for the Input Data Register	CC, AA
t_{ISUE}	Enable Setup Time for the Input Data Register	BB, AA
t_{IHE}	Enable Hold Time for the Input Data Register	BB, AA
t_{ICLR2Q}	Asynchronous Clear-to-Q of the Input Data Register	DD, EE
$t_{IREMCLR}$	Asynchronous Clear Removal Time for the Input Data Register	DD, AA
$t_{IRECCLR}$	Asynchronous Clear Recovery Time for the Input Data Register	DD, AA

* *See Figure 2-15 on page 2-46 for more information.*

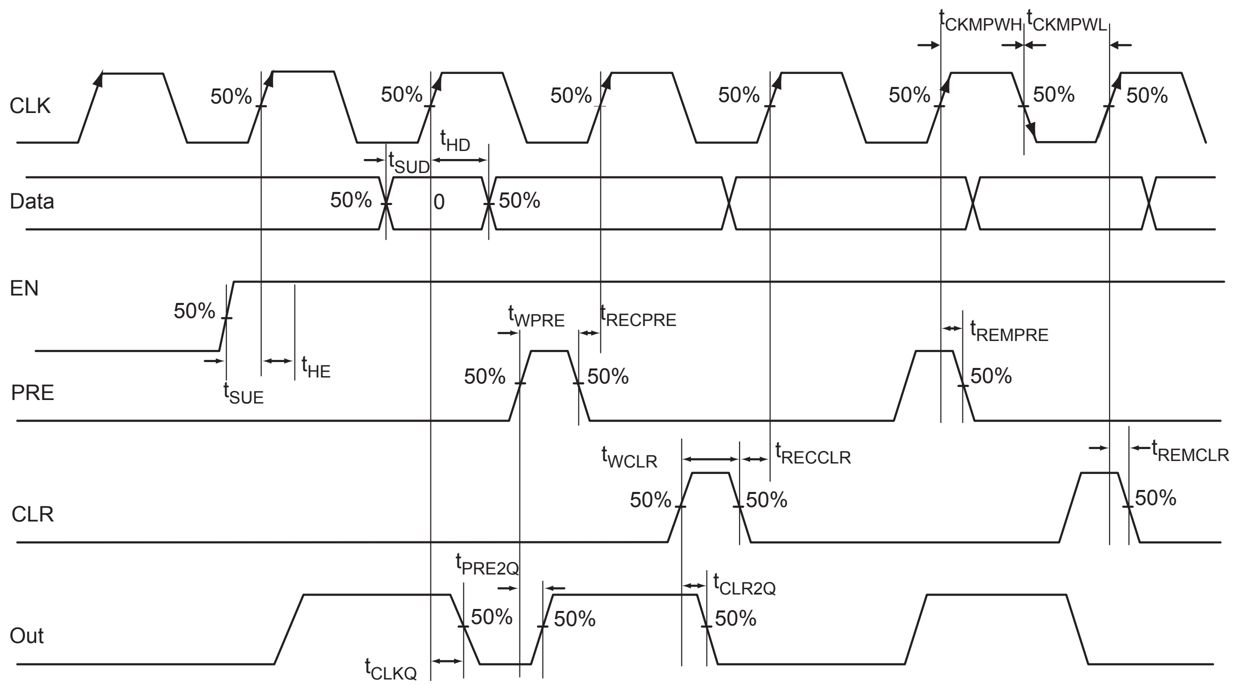


Figure 2-26 • **Timing Model and Waveforms**

Timing Characteristics

Table 2-79 **• Register Delays**
Worst Commercial-Case Conditions: T_J = 85°C, Worst-Case VCC = 1.425 V

Parameter	Description	–1	Std.	Units
t_{CLKQ}	Clock-to-Q of the Core Register	0.56	0.67	ns
t_{SUD}	Data Setup Time for the Core Register	0.44	0.52	ns
t_{HD}	Data Hold Time for the Core Register	0.00	0.00	ns
t_{SUE}	Enable Setup Time for the Core Register	0.46	0.55	ns
t_{HE}	Enable Hold Time for the Core Register	0.00	0.00	ns
t_{CLR2Q}	Asynchronous Clear-to-Q of the Core Register	0.41	0.49	ns
t_{PRE2Q}	Asynchronous Preset-to-Q of the Core Register	0.41	0.49	ns
t_{REMCLR}	Asynchronous Clear Removal Time for the Core Register	0.00	0.00	ns
t_{RECCLR}	Asynchronous Clear Recovery Time for the Core Register	0.23	0.27	ns
t_{REMPRE}	Asynchronous Preset Removal Time for the Core Register	0.00	0.00	ns
t_{RECPRE}	Asynchronous Preset Recovery Time for the Core Register	0.23	0.27	ns
t_{WCLR}	Asynchronous Clear Minimum Pulse Width for the Core Register	0.22	0.22	ns
t_{WPRE}	Asynchronous Preset Minimum Pulse Width for the Core Register	0.22	0.22	ns
t_{CKMPWH}	Clock Minimum Pulse Width High for the Core Register	0.32	0.32	ns
t_{CKMPWL}	Clock Minimum Pulse Width Low for the Core Register	0.36	0.36	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-9 for derating values.

Table 2-88 **• RAM512X18**
Worst Commercial-Case Conditions: T_J = 85°C, Worst-Case VCC = 1.425 V

Parameter	Description	–1	Std.	Units
t_{AS}	Address setup time	0.25	0.30	ns
t_{AH}	Address hold time	0.00	0.00	ns
t_{ENS}	REN, WEN setup time	0.09	0.11	ns
t_{ENH}	REN, WEN hold time	0.06	0.07	ns
t_{DS}	Input data (WD) setup time	0.19	0.22	ns
t_{DH}	Input data (WD) hold time	0.00	0.00	ns
t_{CKQ1}	Clock High to new data valid on RD (output retained, WMODE = 0)	2.19	2.63	ns
t_{CKQ2}	Clock High to new data valid on RD (pipelined)	0.91	1.09	ns
t_{C2CRWH}[1]	Address collision clk-to-clk delay for reliable read access after write on same address—applicable to opening edge	0.38	0.43	ns
t_{C2CWRH}[1]	Address collision clk-to-clk delay for reliable write access after read on same address—applicable to opening edge	0.44	0.50	ns
t_{RSTBQ}	RESET Low to data out Low on RD (flow-through)	0.94	1.12	ns
	RESET Low to data out Low on RD (pipelined)	0.94	1.12	ns
$t_{REMRSTB}$	RESET removal	0.29	0.35	ns
$t_{RECRSTB}$	RESET recovery	1.52	1.83	ns
$t_{MPWRSTB}$	RESET minimum pulse width	0.22	0.22	ns
t_{CYC}	Clock cycle time	3.28	3.28	ns
F_{MAX}	Maximum clock frequency	305	305	MHz

Notes:

1. *For more information, refer to the Simultaneous Read-Write Operations in Dual-Port SRAM for Flash-Based cSoCs and FPGAs application note.*
2. *For the derating values at specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-9 for derating values.*

FIFO

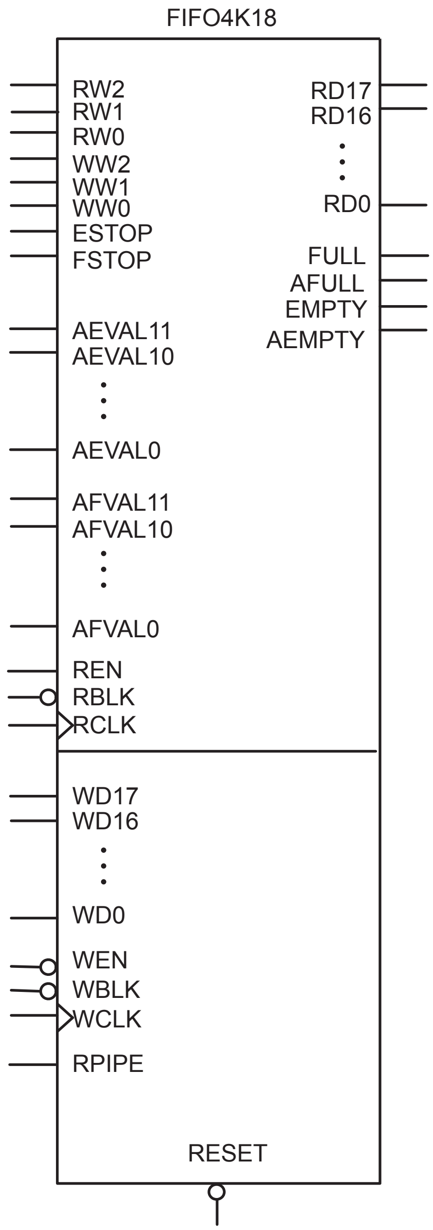


***Figure 2-35* • FIFO Model**

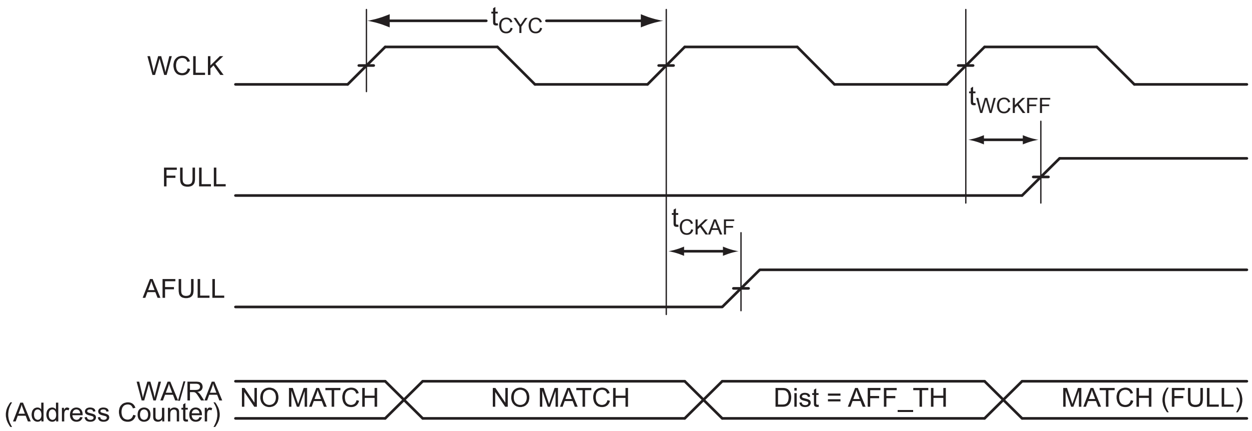


***Figure 2-40* • FIFO FULL Flag and AFULL Flag Assertion**

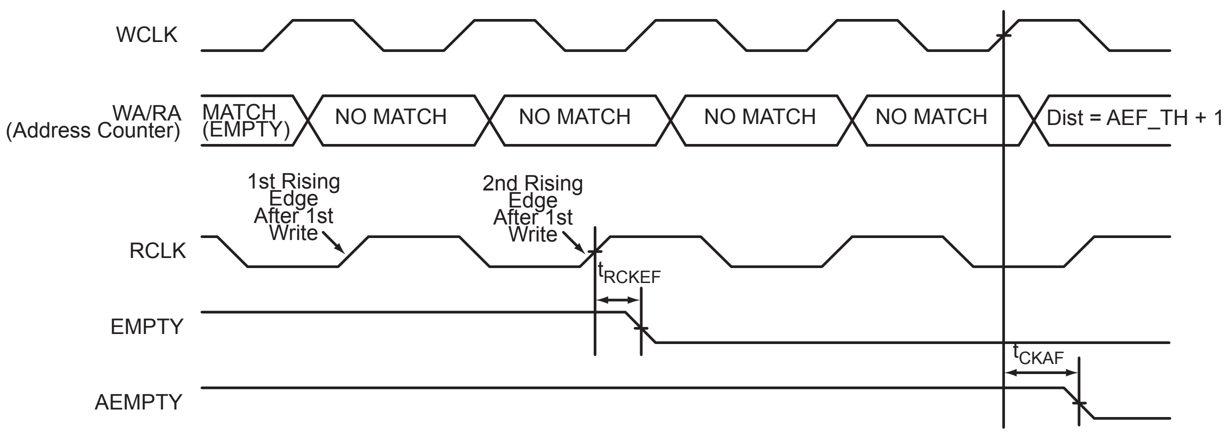


***Figure 2-41* • FIFO EMPTY Flag and AEMPTY Flag Deassertion**

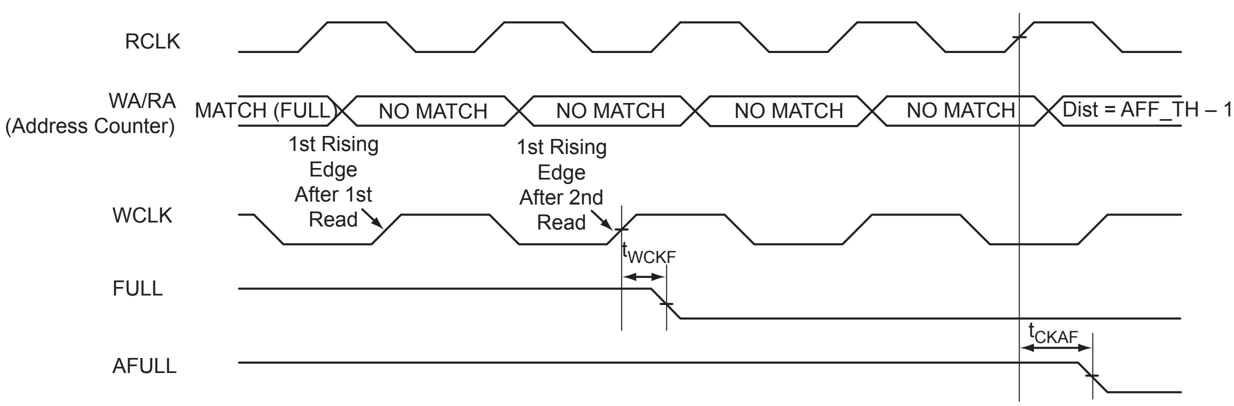


***Figure 2-42* • FIFO FULL Flag and AFULL Flag Deassertion**

Programmable Analog Specifications

Current Monitor

Unless otherwise noted, current monitor performance is specified at 25°C with nominal power supply voltages, with the output measured using the internal voltage reference with the internal ADC in 12-bit mode and 91 Ksps, after digital compensation. All results are based on averaging over 16 samples.

***Table 2-93* • Current Monitor Performance Specification**

Specification	Test Conditions	Min.	Typical	Max.	Units
Input voltage range (for driving ADC over full range)		0 – 48	0 – 50	1 – 51	mV
Analog gain	From the differential voltage across the input pads to the ADC input		50		V/V
Input referred offset voltage	Input referred offset voltage	0	0.1	0.5	mV
	–40ºC to +100ºC	0	0.1	0.5	mV
Gain error	Slope of BFSL vs. 50 V/V		±0.1	±0.5	% nom.
	–40ºC to +100ºC			±0.5	% nom.
Overall Accuracy	Peak error from ideal transfer function, 25°C		±(0.1 + 0.25%)	±(0.4 + 1.5%)	mV plus % reading
Input referred noise	0 VDC input (no output averaging)	0.3	0.4	0.5	mVrms
Common-mode rejection ratio	0 V to 12 VDC common-mode voltage	–86	–87		dB
Analog settling time	To 0.1% of final value (with ADC load)				
	From CM_STB (High)	5			µs
	From ADC_START (High)	5		200	µs
Input capacitance			8		pF
Input biased current	CM[n] or TM[n] pad, –40°C to +100°C over maximum input voltage range (plus is into pad)				
	Strobe = 0; IBIAS on CM[n]		0		µA
	Strobe = 1; IBIAS on CM[n]		1		µA
	Strobe = 0; IBIAS on TM[n]		2		µA
	Strobe = 1; IBIAS on TM[n]		1		µA
Power supply rejection ratio	DC (0 – 10 KHz)	41	42		dB
Incremental operational current monitor power supply current requirements (per current monitor instance, not including ADC or VAREFx)	VCC33A		150		µA
	VCC33AP		140		µA
	VCC15A		50		µA

Note: Under no condition should the TM pad ever be greater than 10 mV above the CM pad. This restriction is applicable only if current monitor is used.

Global I/O Naming Conventions

Gmn (Gxxx) refers to Global I/Os. These Global I/Os are used to connect the input to global networks. Global networks have high fanout and low skew. The naming convention for Global I/Os is as follows:

G = Global

m = Global pin location associated with each CCC on the device:

- A (northwest corner)
- B (northeast corner)
- C (east middle)
- D (southeast corner)
- E (southwest corner)
- F (west middle)

n = Global input MUX and pin number of the associated Global location m—A0, A1, A2, B0, B1, B2, C0, C1, or C2.

Global (GL) I/Os have access to certain clock conditioning circuitry (and the PLL) and/or have direct access to the global network (spines). Additionally, the global I/Os can be used as regular I/Os, since they have identical capabilities.

Unused GL pins are configured as inputs with pull-up resistors. See more detailed descriptions of global I/O connectivity in the clocking resources chapter of the *SmartFusion FPGA Fabric User's Guide* and the clock conditioning circuitry chapter of the *SmartFusion Microcontroller Subsystem User's Guide*.

All inputs other than GC/GF are direct inputs into the quadrant clocks. The inputs to the global network are multiplexed, and only one input can be used as a global input. For example, if GAA0 is used as a quadrant global input, GAA1 and GAA2 are no longer available for input to the quadrant globals. All inputs other than GC/GF are direct inputs into the chip-level globals, and the rest are connected to the quadrant globals. For more details, refer to the Global Input Selections section of the SmartFusion Fabric User Guide.

User Pins

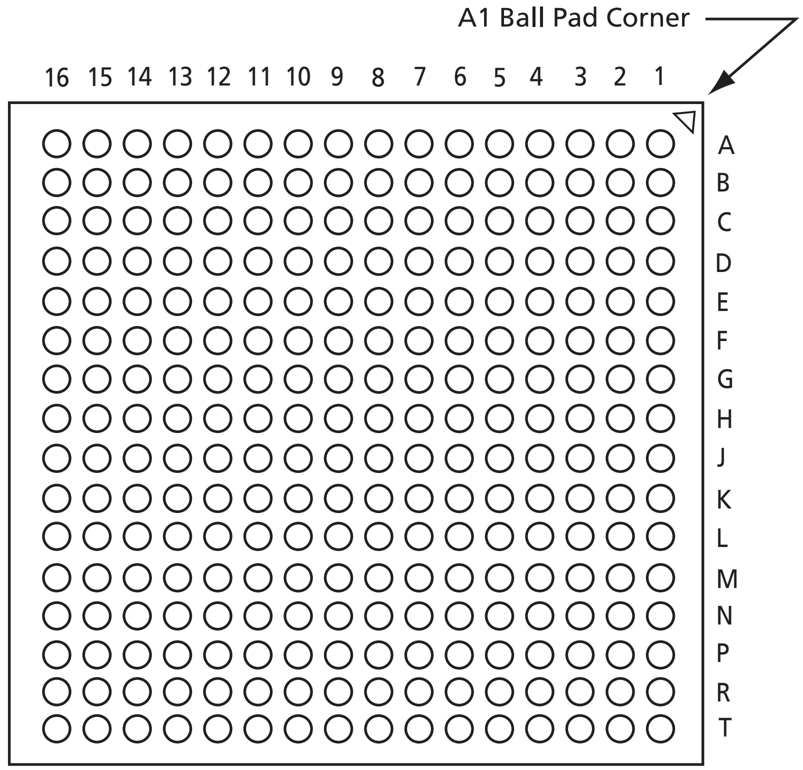
Name	Type	Polarity/Bus Size	Description
GPIO_x	In/out	32	Microcontroller Subsystem (MSS) General Purpose I/O (GPIO). The MSS GPIO pin functions as an input, output, tristate, or bidirectional buffer with configurable interrupt generation and Schmitt trigger support. Input and output signal levels are compatible with the I/O standard selected. Unused GPIO pins are tristated and do not include pull-up or pull-down resistors. During power-up, the used GPIO pins are tristated with no pull-up or pull-down resistors until Sys boot configures them. Some of these pins are also multiplexed with integrated peripherals in the MSS (SPI, I^2C, and UART). These pins are located in Bank-2 (GPIO_16 to GPIO_31) for A2F060, A2F200, and A2F500 devices. GPIOs can be routed to dedicated I/O buffers (MSSIOBUF) or in some cases to the FPGA fabric interface through an IOMUX. This allows GPIO pins to be multiplexed as either I/Os for the FPGA fabric, the ARM® Cortex-M3 or for given integrated MSS peripherals. The MSS peripherals are not multiplexed with each other; they are multiplexed only with the GPIO block. For more information, see the General Purpose I/O Block (GPIO) section in the *SmartFusion Microcontroller Subsystem User's Guide*.
IO	In/out		FPGA user I/O

Pin Number	PQ208	
	A2F200	A2F500
94	ABPS5	ABPS5
95	ABPS4	ABPS4
96	GNDAQ	GNDAQ
97	GNDA	GNDA
98	NC	NC
99	GNDVAREF	GNDVAREF
100	VAREFOUT	VAREFOUT
101	PU_N	PU_N
102	VCC33A	VCC33A
103	PTEM	PTEM
104	PTBASE	PTBASE
105	SPI_0_DO/GPIO_16	SPI_0_DO/GPIO_16
106	SPI_0_DI/GPIO_17	SPI_0_DI/GPIO_17
107	SPI_0_CLK/GPIO_18	SPI_0_CLK/GPIO_18
108	SPI_0_SS/GPIO_19	SPI_0_SS/GPIO_19
109	UART_0_RXD/GPIO_21	UART_0_RXD/GPIO_21
110	UART_0_TXD/GPIO_20	UART_0_TXD/GPIO_20
111	UART_1_RXD/GPIO_29	UART_1_RXD/GPIO_29
112	UART_1_TXD/GPIO_28	UART_1_TXD/GPIO_28
113	VCC	VCC
114	VCCMSSIOB2	VCCMSSIOB2
115	GND	GND
116	I2C_1_SDA/GPIO_30	I2C_1_SDA/GPIO_30
117	I2C_1_SCL/GPIO_31	I2C_1_SCL/GPIO_31
118	I2C_0_SDA/GPIO_22	I2C_0_SDA/GPIO_22
119	I2C_0_SCL/GPIO_23	I2C_0_SCL/GPIO_23
120	GNDENVM	GNDENVM
121	VCCENVM	VCCENVM
122	JTAGSEL	JTAGSEL
123	TCK	TCK
124	TDI	TDI

Notes:

1. *Shading denotes pins that do not have completely identical functions from density to density. For example, the bank assignment can be different for an I/O, or the function might be available only on a larger density device.*
2. **: Indicates that the signal assigned to the pins as a CLKBUF/CLKBUF_LVPECL/CLKBUF_LVDS goes through a glitchless mux. In order for the glitchless mux to operate correctly, the signal must be a free-running clock signal. Refer to the 'Glitchless MUX' section in the SmartFusion Microcontroller Subsystem User's Guide for more details.*

FG256



Note

For Package Manufacturing and Environmental information, visit the Resource Center at http://www.microsemi.com/soc/products/solutions/package/docs.aspx.

Pin No.	FG256		
	A2F060 Function	**A2F200 Function**	**A2F500 Function**
D15	GCA1/IO20PDB0V0	IO24NDB1V0	IO33NDB1V0
D16	VCCFPGAIOB1	VCCFPGAIOB1	VCCFPGAIOB1
E1	EMC_DB[13]/IO44PDB5V0	EMC_DB[13]/GAC2/IO70PDB5V0	EMC_DB[13]/GAC2/IO87PDB5V0
E2	EMC_DB[12]/IO44NDB5V0	EMC_DB[12]/IO70NDB5V0	EMC_DB[12]/IO87NDB5V0
E3	GFA2/IO42PDB5V0	GFA2/IO68PDB5V0	GFA2/IO85PDB5V0
E4	EMC_DB[10]/IO43NPB5V0	EMC_DB[10]/IO69NPB5V0	EMC_DB[10]/IO86NPB5V0
E5	GNDQ	GNDQ	GNDQ
E6	GND	GND	GND
E7	VCCFPGAIOB0	VCCFPGAIOB0	VCCFPGAIOB0
E8	GND	GND	GND
E9	VCCFPGAIOB0	VCCFPGAIOB0	VCCFPGAIOB0
E10	GND	GND	GND
E11	VCCFPGAIOB0	VCCFPGAIOB0	VCCFPGAIOB0
E12	GCB2/IO22PDB1V0	GCA1/IO28PDB1V0	GCA1/IO36PDB1V0 *
E13	VCCFPGAIOB1	VCCFPGAIOB1	VCCFPGAIOB1
E14	GCA2/IO21PDB1V0	GCB1/IO27PDB1V0	GCB1/IO34PDB1V0
E15	GCC2/IO23PDB1V0	GDC1/IO29PDB1V0	GDC1/IO38PDB1V0
E16	IO23NDB1V0	GDC0/IO29NDB1V0	GDC0/IO38NDB1V0
F1	EMC_DB[9]/IO40PDB5V0	EMC_DB[9]/GEC1/IO63PDB5V0	EMC_DB[9]/GEC1/IO80PDB5V0
F2	GND	GND	GND
F3	GFB2/IO42NDB5V0	GFB2/IO68NDB5V0	GFB2/IO85NDB5V0
F4	VCCFPGAIOB5	VCCFPGAIOB5	VCCFPGAIOB5
F5	EMC_DB[11]/IO43PPB5V0	EMC_DB[11]/IO69PPB5V0	EMC_DB[11]/IO86PPB5V0
F6	VCCFPGAIOB5	VCCFPGAIOB5	VCCFPGAIOB5
F7	GND	GND	GND
F8	VCC	VCC	VCC
F9	GND	GND	GND
F10	VCC	VCC	VCC
F11	GND	GND	GND
F12	IO22NDB1V0	GCA0/IO28NDB1V0	GCA0/IO36NDB1V0 *
F13	NC	GNDQ	GNDQ

Notes:

1. *Shading denotes pins that do not have completely identical functions from density to density. For example, the bank assignment can be different for an I/O, or the function might be available only on a larger density device.*
2. **: Indicates that the signal assigned to the pins as a CLKBUF/CLKBUF_LVPECL/CLKBUF_LVDS goes through a glitchless mux. In order for the glitchless mux to operate correctly, the signal must be a free-running clock signal. Refer to the 'Glitchless MUX' section in the SmartFusion Microcontroller Subsystem User's Guide for more details.*

Pin No.	FG256		
	A2F060 Function	A2F200 Function	A2F500 Function
H13	TDO	TDO	TDO
H14	TDI	TDI	TDI
H15	JTAGSEL	JTAGSEL	JTAGSEL
H16	GND	GND	GND
J1	EMC_DB[4]/IO38NPB5V0	EMC_DB[4]/GEA0/IO61NPB5V0	EMC_DB[4]/GEA0/IO78NPB5V0
J2	EMC_DB[3]/IO37PDB5V0	EMC_DB[3]/GEC2/IO60PDB5V0	EMC_DB[3]/GEC2/IO77PDB5V0
J3	EMC_DB[2]/IO37NDB5V0	EMC_DB[2]/IO60NDB5V0	EMC_DB[2]/IO77NDB5V0
J4	GNDRCOSC	GNDRCOSC	GNDRCOSC
J5	NC	GNDQ	GNDQ
J6	GND	GND	GND
J7	VCC	VCC	VCC
J8	GND	GND	GND
J9	VCC	VCC	VCC
J10	GND	GND	GND
J11	VCCMSSIOB2	VCCMSSIOB2	VCCMSSIOB2
J12	I2C_0_SCL/GPIO_23	I2C_0_SCL/GPIO_23	I2C_0_SCL/GPIO_23
J13	I2C_0_SDA/GPIO_22	I2C_0_SDA/GPIO_22	I2C_0_SDA/GPIO_22
J14	I2C_1_SCL/GPIO_31	I2C_1_SCL/GPIO_31	I2C_1_SCL/GPIO_31
J15	VCCMSSIOB2	VCCMSSIOB2	VCCMSSIOB2
J16	I2C_1_SDA/GPIO_30	I2C_1_SDA/GPIO_30	I2C_1_SDA/GPIO_30
K1	GPIO_1/IO32RSB4V0	MAC_MDIO/IO49RSB4V0	MAC_MDIO/IO58RSB4V0
K2	GPIO_0/IO33RSB4V0	MAC_MDC/IO48RSB4V0	MAC_MDC/IO57RSB4V0
K3	VCCMSSIOB4	VCCMSSIOB4	VCCMSSIOB4
K4	MSS_RESET_N	MSS_RESET_N	MSS_RESET_N
K5	VCCRCOSC	VCCRCOSC	VCCRCOSC
K6	VCCMSSIOB4	VCCMSSIOB4	VCCMSSIOB4
K7	GND	GND	GND
K8	VCC	VCC	VCC
K9	GND	GND	GND
K10	VCC	VCC	VCC
K11	GND	GND	GND

Notes:

1. *Shading denotes pins that do not have completely identical functions from density to density. For example, the bank assignment can be different for an I/O, or the function might be available only on a larger density device.*
2. **: Indicates that the signal assigned to the pins as a CLKBUF/CLKBUF_LVPECL/CLKBUF_LVDS goes through a glitchless mux. In order for the glitchless mux to operate correctly, the signal must be a free-running clock signal. Refer to the 'Glitchless MUX' section in the SmartFusion Microcontroller Subsystem User's Guide for more details.*

Pin No.	FG256		
	A2F060 Function	**A2F200 Function**	**A2F500 Function**
T9	VAREF0	VAREF1	VAREF1
T10	ABPS0	ABPS6	ABPS6
T11	NC	ABPS5	ABPS5
T12	NC	SDD1	SDD1
T13	GNDVAREF	GNDVAREF	GNDVAREF
T14	GNDMAINXTAL	GNDMAINXTAL	GNDMAINXTAL
T15	VCCLPXTAL	VCCLPXTAL	VCCLPXTAL
T16	PU_N	PU_N	PU_N

Notes:

1. *Shading denotes pins that do not have completely identical functions from density to density. For example, the bank assignment can be different for an I/O, or the function might be available only on a larger density device.*
2. **: Indicates that the signal assigned to the pins as a CLKBUF/CLKBUF_LVPECL/CLKBUF_LVDS goes through a glitchless mux. In order for the glitchless mux to operate correctly, the signal must be a free-running clock signal. Refer to the 'Glitchless MUX' section in the SmartFusion Microcontroller Subsystem User's Guide for more details.*

Revision	Changes	Page
Revision 3 (continued)	Two notes were added to the "Supply Pins" table (SAR 27109): *1. The following supplies should be connected together while following proper noise filtering practices: VCC33A, VCC33ADCx, VCC33AP, VCC33SDDx, VCCMAINXTAL, and VCCLPXTAL.* *2. The following 1.5 V supplies should be connected together while following proper noise filtering practices: VCC, VCC15A, and VCC15ADCx.*	5-1
	The descriptions for the "VCC33N", "NCAP", and "PCAP" pins were revised to include information on what to do if analog SCB features and SDDs are not used (SAR 26744).	5-2, 5-9, 5-9
	Information was added to the "User Pins" table regarding tristating of used and unused GPIO pins. The IO portion of the table was revised to state that unused I/O pins are disabled by Libero IDE software and include a weak pull-up resistor (SAR 26890). Information was added regarding behavior of used I/O pins during power-up.	5-6
	The type for "EMC_RW_N" was changed from In/out to Out (SAR 25113).	5-12
	A note was added to the "Analog Front-End (AFE)" table stating that unused analog inputs should be grounded (SAR 26744).	5-14
	The "TQ144" section is new, with pin tables for A2F200 and A2F500 (SAR 27044).	5-18
	The "FG256" pin table was replaced and now includes "Handling When Unused" information (SAR 27709).	5-42
Revision 2 (May 2010)	Embedded nonvolatile flash memory (eNVM) was changed from "64 to 512 Kbytes" to "128 to 512 Kbytes" in the "Microcontroller Subsystem (MSS)" section and "SmartFusion cSoC Family Product Table" (SAR 26005).	I, II
	The main oscillator range of values was changed to "32 KHz to 20 MHz" in the "Microcontroller Subsystem (MSS)" section and the "SmartFusion cSoC Family Product Table" (SAR 24906).	I, II
	The value for t_{PD} was changed from 50 ns to 15 ns for the high-speed voltage comparators listed in the "Analog Front-End (AFE)" section (SAR 26005).	I
	The number of PLLs for A2F200 was changed from 2 to 1 in the "SmartFusion cSoC Family Product Table" (SAR 25093).	II
	Values for direct analog input, total analog input, and total I/Os were updated for the FG256 package, A2F060, in the "Package I/Os: MSS + FPGA I/Os" table. The Max. column was removed from the table (SAR 26005).	III
	The Speed Grade section of the "Product Ordering Codes" table was revised (SAR 25257).	VI
Revision 1 (March 2010)	The "Product Ordering Codes" table was revised to add "blank" as an option for lead-free packaging and application (junction temperature range).	VI
	Table 2-3 • Recommended Operating Conditions[5,6] was revised. Ta (ambient temperature) was replaced with T_J (junction temperature).	2-3
	PDC5 was deleted from Table 2-15 • Different Components Contributing to the Static Power Consumption in SmartFusion cSoCs.	2-13
	The formulas in the footnotes for Table 2-29 • I/O Weak Pull-Up/Pull-Down Resistances were revised.	2-27
	The values for input biased current were revised in Table 2-93 • Current Monitor Performance Specification.	2-78
Revision 0 (March 2010)	The "Analog Front-End (AFE)" section was updated to change the throughput for 10-bit mode from 600 Ksps to 550 Ksps.	I